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Date: 06 June 2023

Origin: International

Latest date for receipt of comments: 13 September 2023

Project No. 2023/01197

Responsible committee: EPL/47 Semiconductors

Interested committees:

Title: BS IEC 63505 Guidelines for measuring the threshold voltage (VT) of SiC MOSFETs

Please notify the secretary if you are aware of any keywords that might assist in classifying or identifying the standard or if the content of this standard

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- ii) affects other national standard(s)
- iii) requires additional national guidance or information

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Introduction

This draft standard is based on national and international discussions. Your comments on this draft are invited and will assist in the preparation of the consequent standard.

For international standards, comments will be reviewed by the relevant UK national committee before sending the consensus UK vote and comments to the international committee, which will then decide appropriate action. If the international standard is approved, it is usual for the text to be published as a British Standard.

For national standards, comments will be reviewed by the relevant UK national committee and the resulting standards published as a British Standard.

UK Vote

Please indicate whether you consider the UK should submit a negative (with supporting technical reasons) or positive vote on this draft. Please indicate if you are aware of any reason why this draft standard should not be published as a British Standard.

Submission of Comments

- **Annotated drafts are not acceptable and will be rejected.**
- All comments should be submitted online at <https://standardsdevelopment.bsigroup.com/>. You will need to register in order to comment.

Template for comments and secretariat observations

Date: xx/xx/20xx	Document: ISO/DIS xxxx
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1	2	(3)	4	5	(6)	7
MB	Clause No./ Subclause No./Annex (e.g. 3.1)	Paragraph/Figure/ Table/Note	Type of comment	Commend (justification for change) by the MB	Proposed change by the MB	Secretariat observations on each comment submitted
	3.1	Definition 1	ed	Definition is ambiguous and needs clarifying.	Amend to read '...so that the mains connector to which no connection...'	
	6.4	Paragraph 2	te	The use of the UV photometer as an alternative cannot be supported as serious problems have been encountered in its use in the UK.	Delete reference to UV photometer.	



47/2806/CDV

COMMITTEE DRAFT FOR VOTE (CDV)

PROJECT NUMBER:

IEC 63505 ED1

DATE OF CIRCULATION:

2023-07-21

CLOSING DATE FOR VOTING:

2023-10-13

SUPERSEDES DOCUMENTS:

IEC TC 47 : SEMICONDUCTOR DEVICES	
SECRETARIAT: Korea, Republic of	SECRETARY: Mr Cheolung Cha
OF INTEREST TO THE FOLLOWING COMMITTEES: TC 91, TC 104	PROPOSED HORIZONTAL STANDARD: ☐ Other TC/SCs are requested to indicate their interest, if any, in this CDV to the secretary.
FUNCTIONS CONCERNED: ☐ EMC ☐ ENVIRONMENT ☐ QUALITY ASSURANCE ☐ SAFETY	
☐ SUBMITTED FOR CENELEC PARALLEL VOTING	☒ NOT SUBMITTED FOR CENELEC PARALLEL VOTING

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Recipients of this document are invited to submit, with their comments, notification of any relevant patent rights of which they are aware and to provide supporting documentation.

Recipients of this document are invited to submit, with their comments, notification of any relevant "In Some Countries" clauses to be included should this proposal proceed. Recipients are reminded that the CDV stage is the final stage for submitting ISC clauses. (SEE [AC/22/2007](#) OR [NEW GUIDANCE DOC](#)).

TITLE:

Guidelines for measuring the threshold voltage (VT) of SiC MOSFETs

PROPOSED STABILITY DATE: 2027

NOTE FROM TC/SC OFFICERS:

This CDV is based upon JEDEC document JEP183 (title: GUIDELINES FOR MEASURING THE THRESHOLD VOLTAGE (VT) OF SiC MOSFETs) and is circulated according to the IEC fast-track procedure (see F.2 of ISO/IEC Directives, Part 1, 2021). This document is proposed by the US National Committee and WG8 at the November 2022 meeting approved fast-track procedure as was presented to TC47 Plenary at the November 2022 Plenary.

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